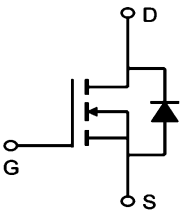
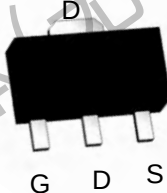
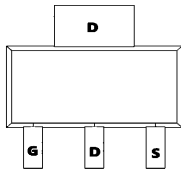




TM08N03SI

N-Channel Enhancement Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features $V_{DS} = 30V$ $I_D = 8.0A$ $R_{DS(ON)} = 20m\Omega$ (typ.) @ $V_{GS} = 10V$ 100% UIS Tested 100% R_g Tested																																							
SI:SOT-89-3L  Marking: HD36																																								
Absolute Maximum Ratings ($T_c = 25^{\circ}C$ Unless Otherwise Noted)																																								
<table><tr><th>Symbol</th><th>Parameter</th><th>Rating</th><th>Units</th></tr><tr><td>V_{DS}</td><td>Drain-Source Voltage</td><td>30</td><td>V</td></tr><tr><td>V_{GS}</td><td>Gate-Source Voltage</td><td>± 20</td><td>V</td></tr><tr><td>$I_D@T_c=25^{\circ}C$</td><td>Continuous Drain Current, V_{GS} @ 10V¹</td><td>8</td><td>A</td></tr><tr><td>$I_D@T_c=100^{\circ}C$</td><td>Continuous Drain Current, V_{GS} @ 10V¹</td><td>4.8</td><td>A</td></tr><tr><td>I_{DM}</td><td>Pulsed Drain Current²</td><td>30.8</td><td>A</td></tr><tr><td>EAS</td><td>Single Pulse Avalanche Energy³</td><td>25</td><td>mJ</td></tr><tr><td>P_D</td><td>Total Power Dissipation³</td><td>1.25</td><td>W</td></tr><tr><td>T_{STG}</td><td>Storage Temperature Range</td><td>-55 to 150</td><td>$^{\circ}C$</td></tr><tr><td>T_J</td><td>Operating Junction Temperature Range</td><td>-55 to 150</td><td>$^{\circ}C$</td></tr></table>	Symbol	Parameter	Rating	Units	V_{DS}	Drain-Source Voltage	30	V	V_{GS}	Gate-Source Voltage	± 20	V	$I_D@T_c=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	8	A	$I_D@T_c=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	4.8	A	I_{DM}	Pulsed Drain Current ²	30.8	A	EAS	Single Pulse Avalanche Energy ³	25	mJ	P_D	Total Power Dissipation ³	1.25	W	T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$	T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
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Thermal Data																																								
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TM08N03SI
N-Channel Enhancement Mosfet
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		T _J =55°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.8	1.5	2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)}	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =5.7A	-	20	23	mΩ
		V _{GS} =4.5V, I _{DS} =5A	-	24	32	
Body Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.7	1.0	V
Dynamic Characteristics						
R _G	Gate Resistance	F=1MHz, Open drain	-	4.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	416	-	pF
C _{oss}	Output Capacitance		-	62	-	
C _{rss}	Reverse transfer capacitance		-	40	-	
t _{d(ON)}	Turn-on delay Time	V _{GS} =10V ,V _{DS} =15V R _G =6Ω, I _D =1A,R _L =10Ω	-	7	15	nS
t _r	Turn-on rise Time		-	10	20	
t _{d(OFF)}	Turn-off delay Time		-	20	40	
t _f	Turn-off rise Time		-	11	20	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =1.6A	-	6	-	nC
Q _{gs}	Gate-Source Charge		-	1.7	-	
Q _{gd}	Gate-Drain Charge		-	3.2	-	

Note: 1. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

2. Static parameters are based on package level with recommended wire bonding

Typical Performance Characteristics

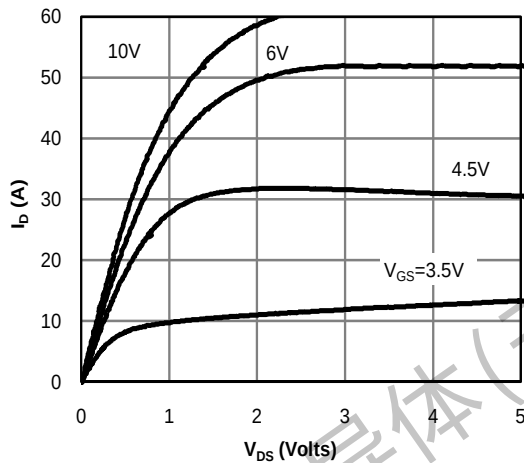


Fig 1: On-Region Characteristics

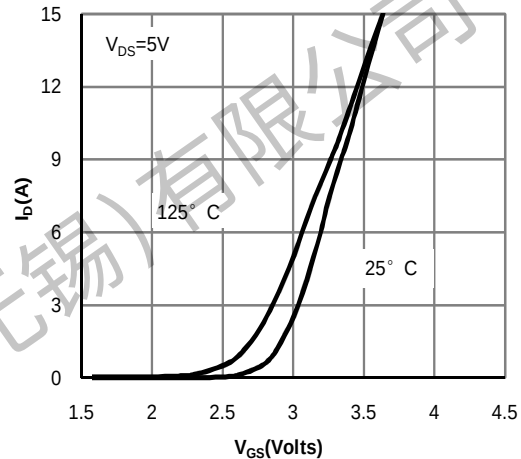


Figure 2: Transfer Characteristics

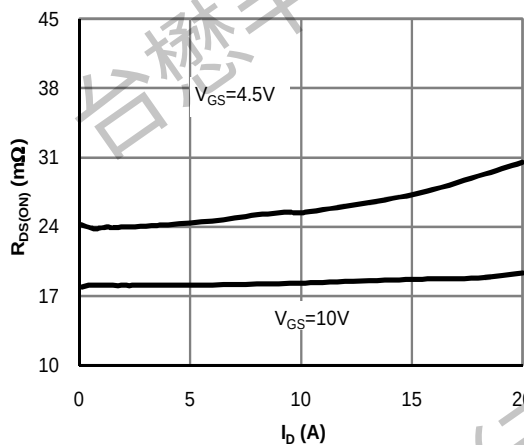


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

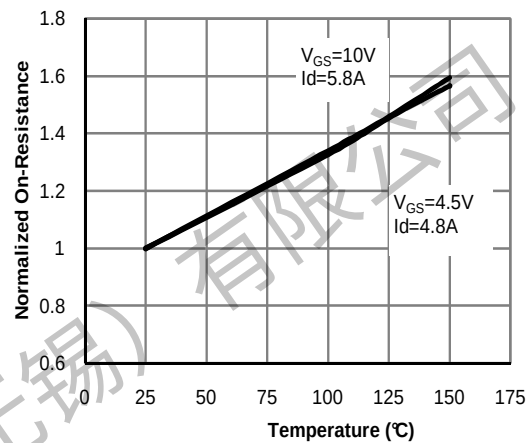


Figure 4: On-Resistance vs. Junction Temperature

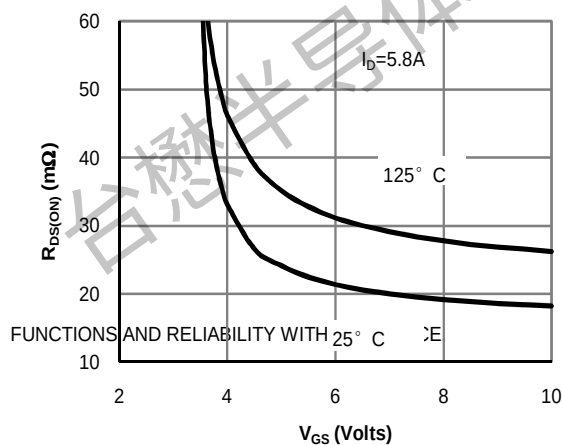


Figure 5: On-Resistance vs. Gate-Source Voltage

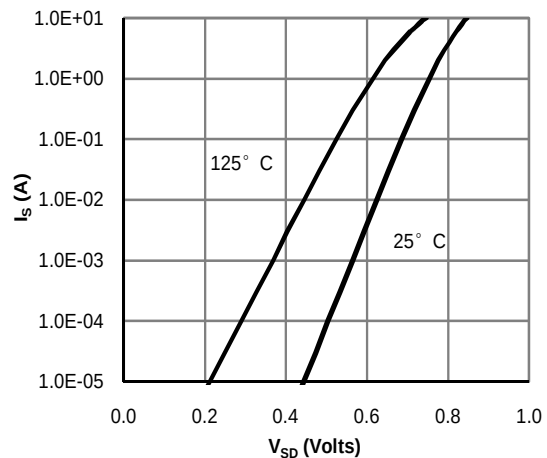


Figure 6: Body-Diode Characteristics

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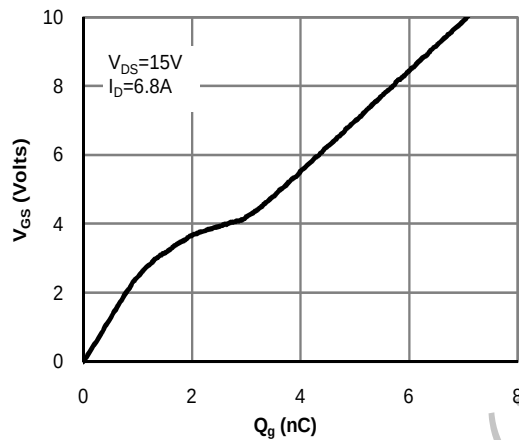


Figure 7: Gate-Charge Characteristics

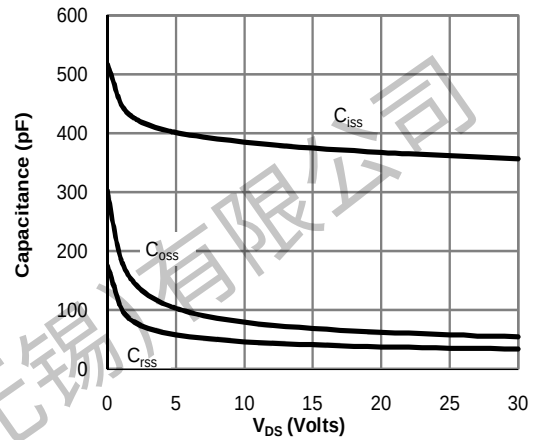


Figure 8: Capacitance Characteristics

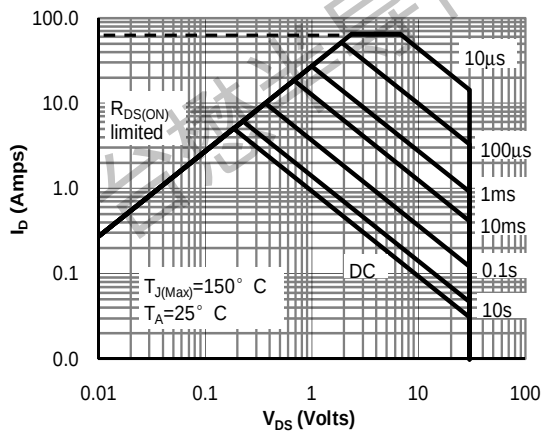


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

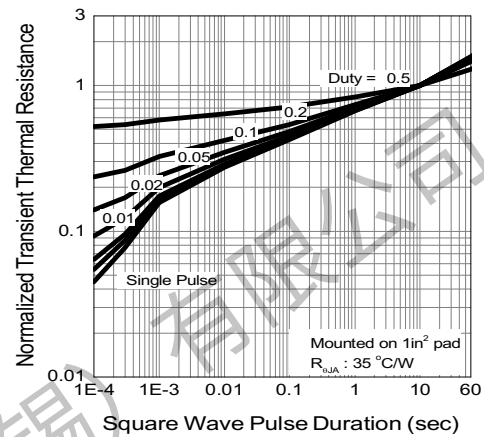


Figure 10: Thermal Transient Impedance

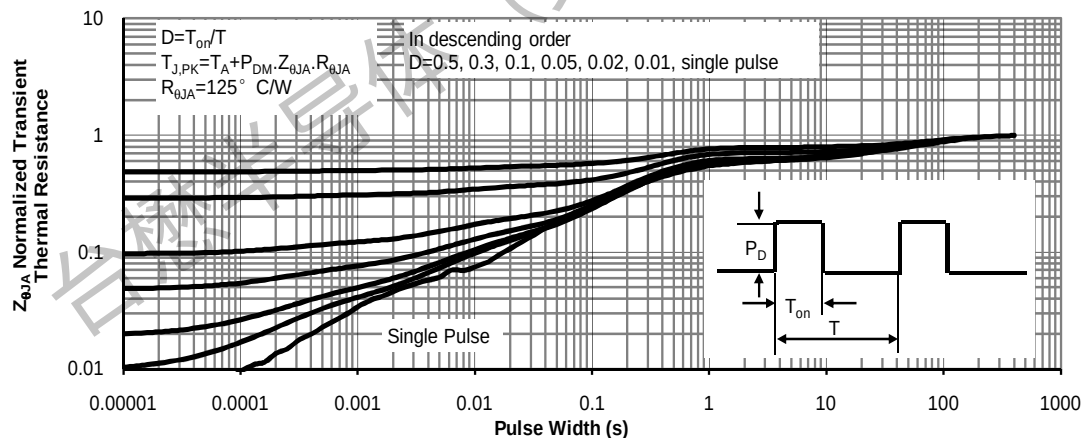
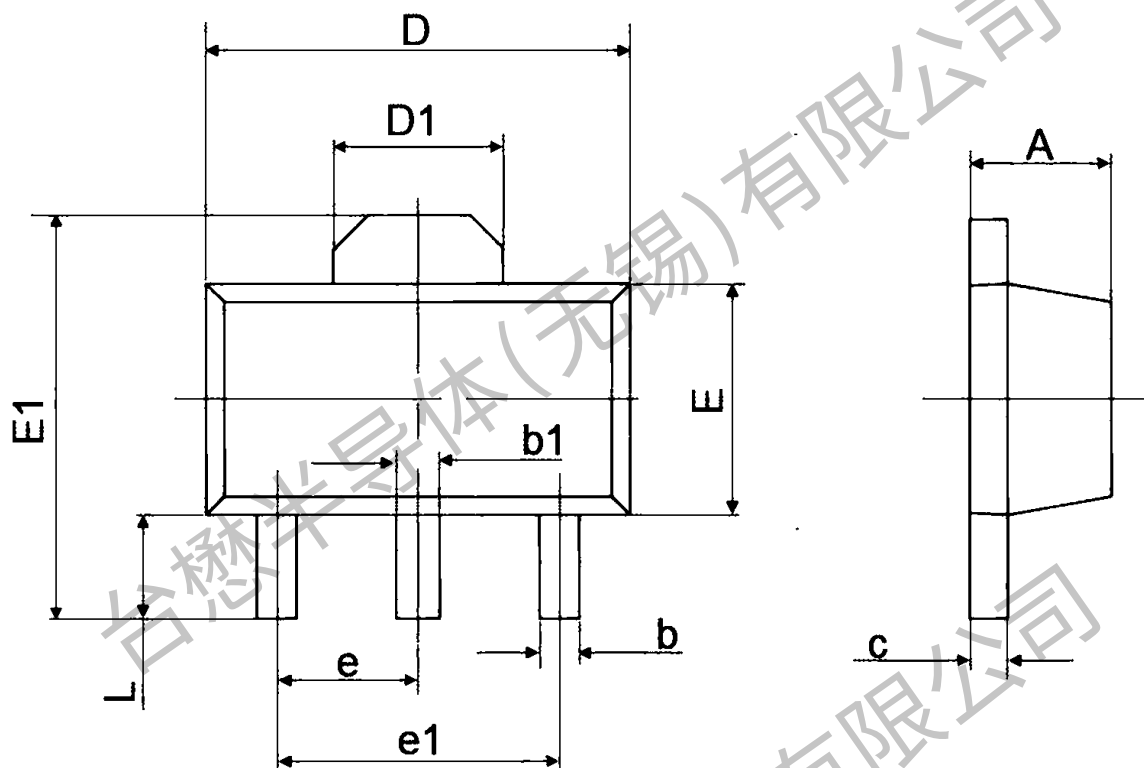


Figure 11: Normalized Maximum Transient Thermal Impedance

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Package Mechanical Data:SOT-89-3L

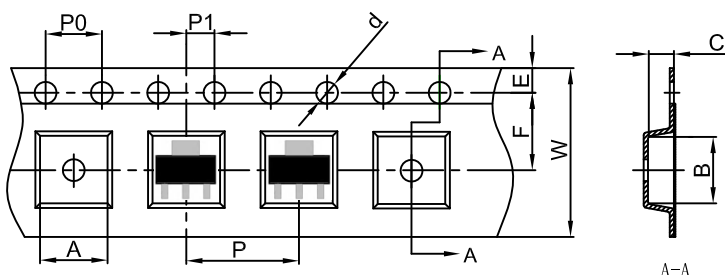


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

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SOT-89-3L Embossed Carrier Tape



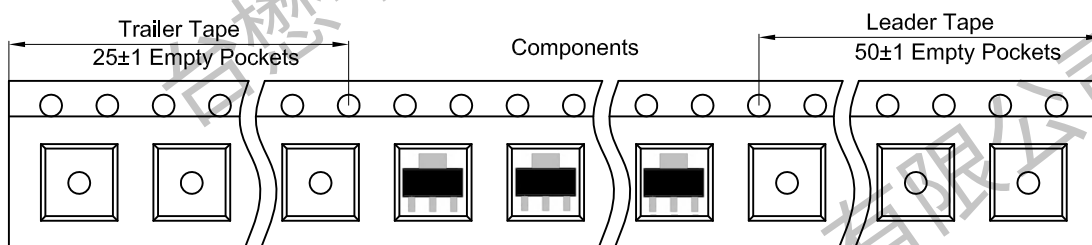
Packaging Description:

SOT-89-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 1,000 units per 7" or 18.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

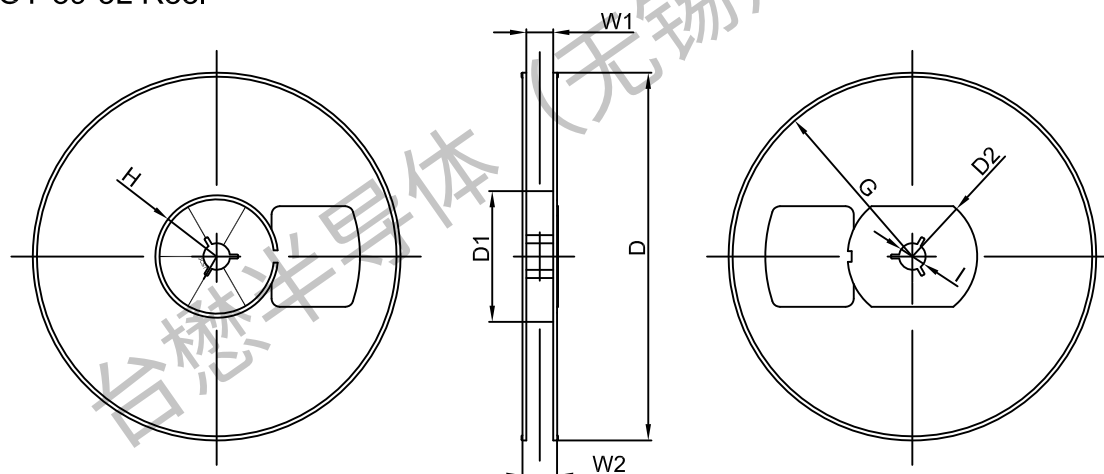
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-89-3L	4.85	4.45	1.85	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOT-89-3L Tape Leader and Trailer



SOT-89-3L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	R32.00	R86.50	R30.00	Ø13.00	13.20	16.50

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
1000 pcs	7 inch	10,000 pcs	205×195×220	40,000 pcs	430×415×240	

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Revision history:

Date	Rev	Description	Page
2023.05.17	23.05	Original	